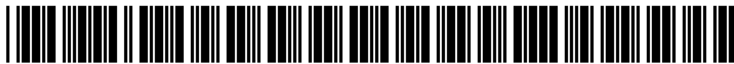

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(54) **TECHNIQUE TO CONTROL TUNNELING CURRENTS IN DRAM CAPACITORS, CELLS, AND DEVICES**

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(60) Continuation of application No. 11/267,009, filed on Nov. 4, 2005, now Pat. No. 7,235,837, which is a continuation of application No. 10/721,585, filed on Nov. 25, 2003, now Pat. No. 6,979,607, which is a division of application No. 09/945,310, filed on Aug. 30, 2001, now Pat. No. 6,664,589.

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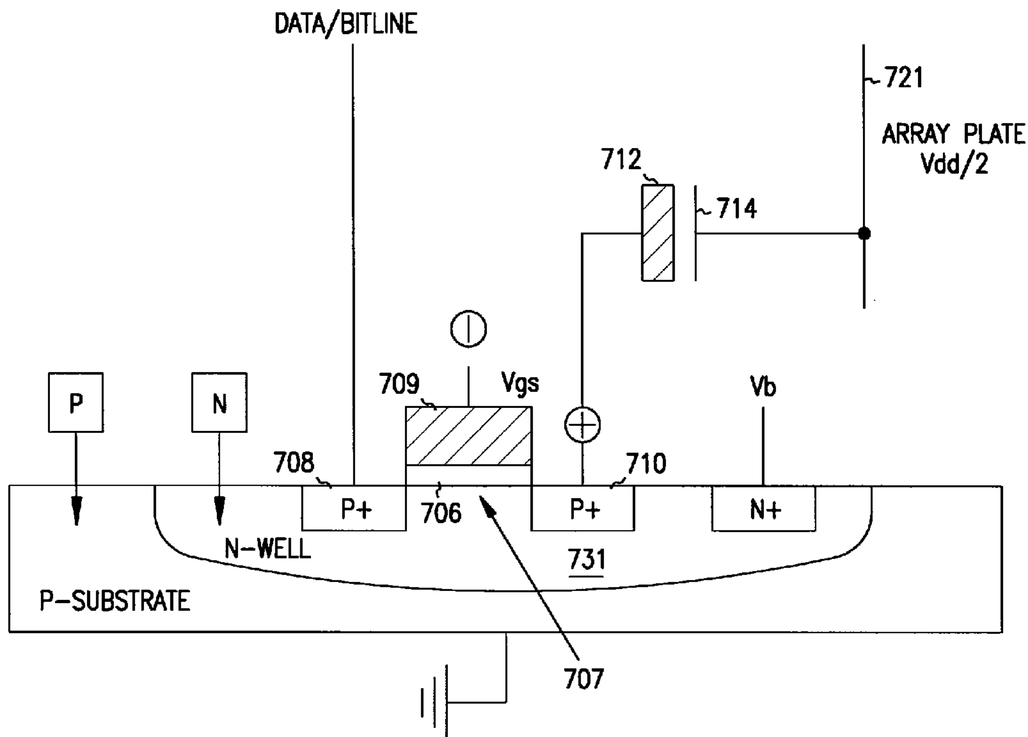
(52) **U.S. Cl.** **257/296**; 257/E27

(57) **ABSTRACT**

Structures and methods are provided for the use with PMOS devices. Materials with large electron affinities or work functions are provided for structures such as gates. A memory cell is provided that utilizes materials with work functions larger than n-type doped polysilicon (4.1 eV) or aluminum metal (4.1 eV) for gates or capacitor plates.



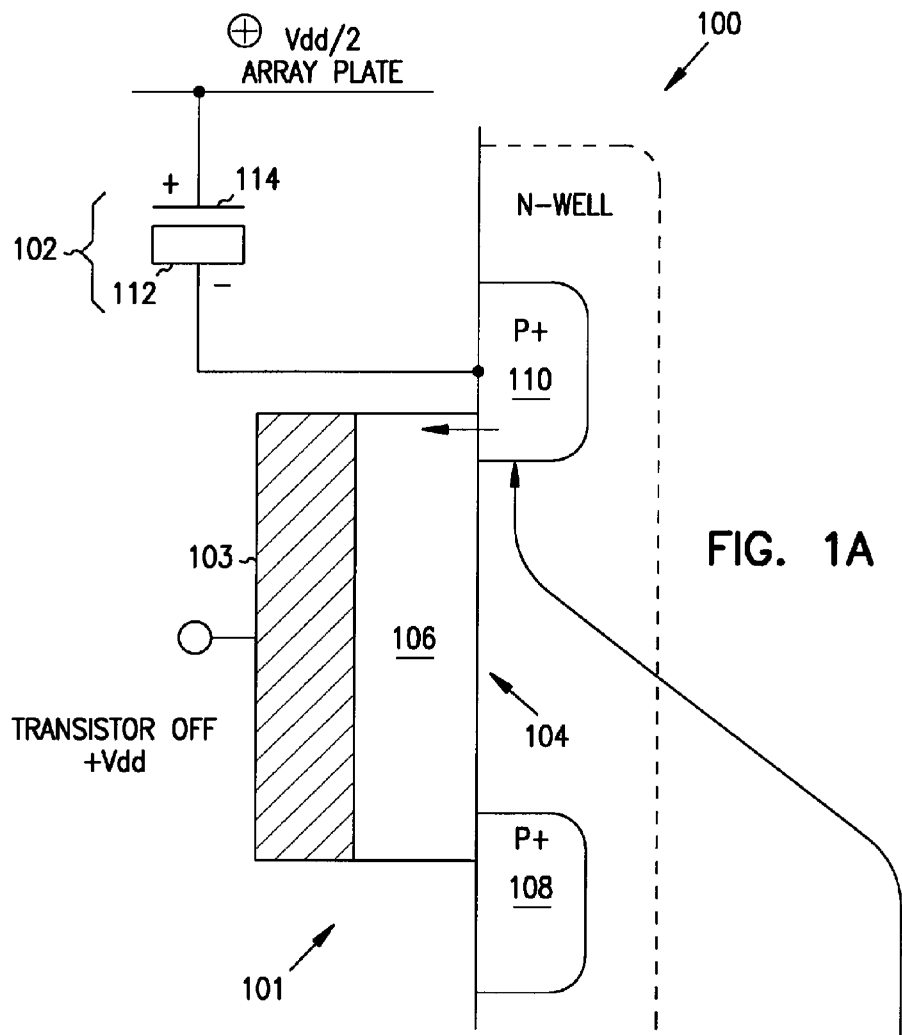


FIG. 1A

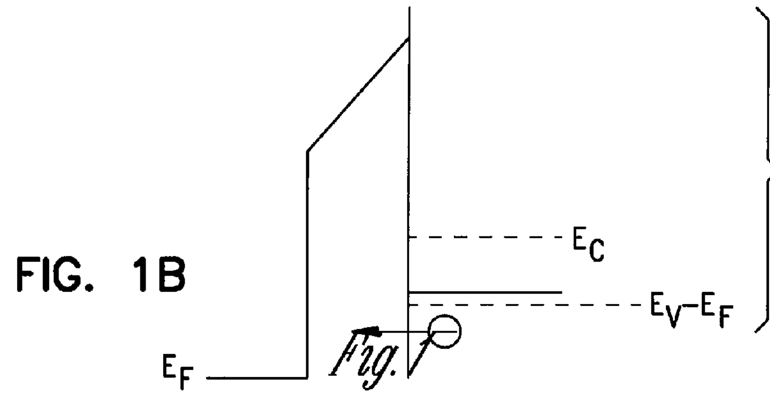
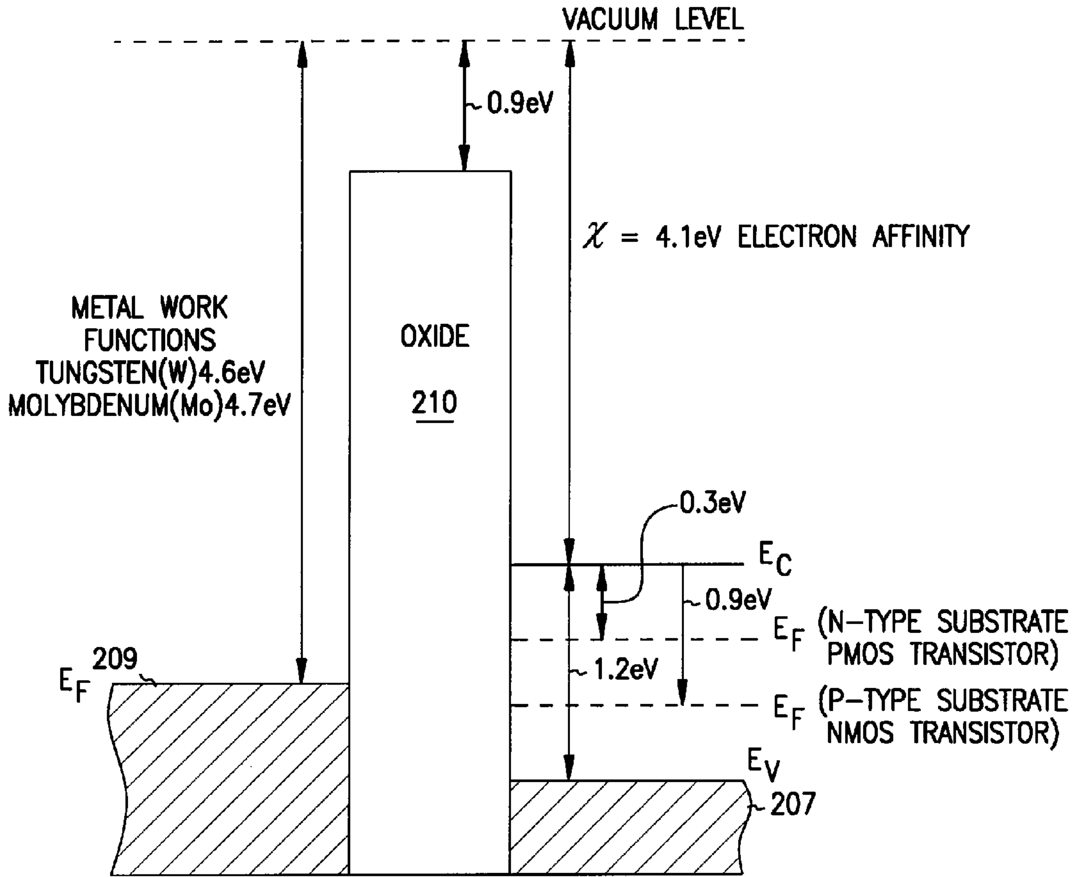


FIG. 1B



"MID-GAP" METALS USED FOR OPTIMIZING NMOS AND PMOS TRANSISTOR THRESHOLDS VOLTAGES; METAL SEMICONDUCTOR WORK FUNCTION DIFFERENCES

NMOS: Φ_{ms} = 4.7−5.0eV = −0.3V

PMOS: Φ_{ms} = 4.7−4.4eV = +0.3V

FIG. 2
(PRIOR ART)

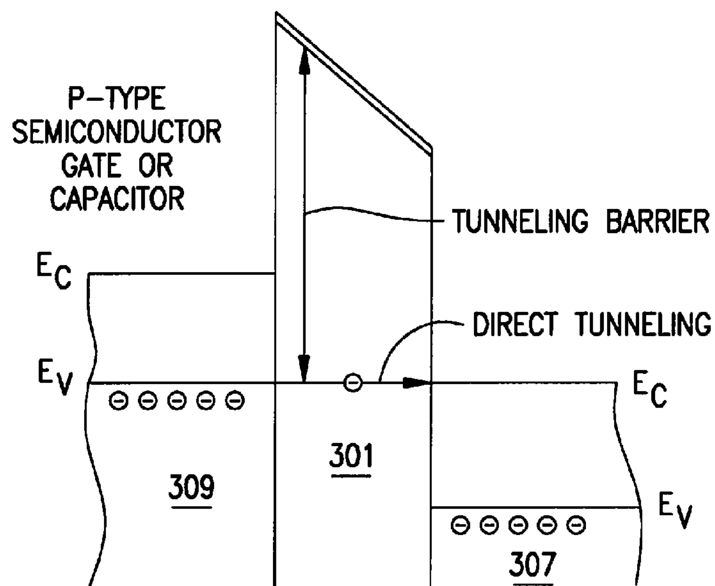


FIG. 3A

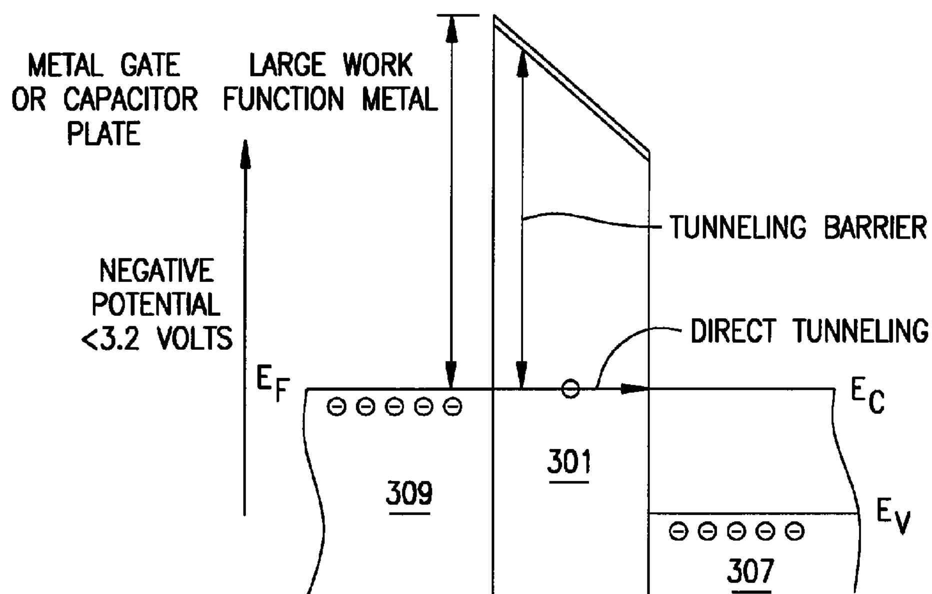


FIG. 3B

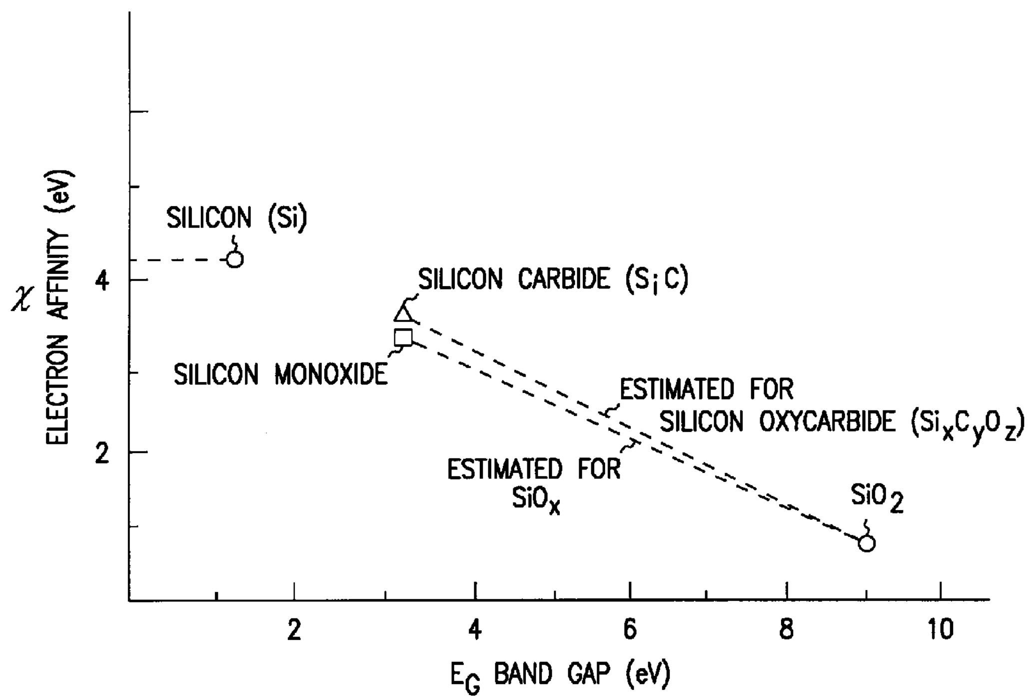
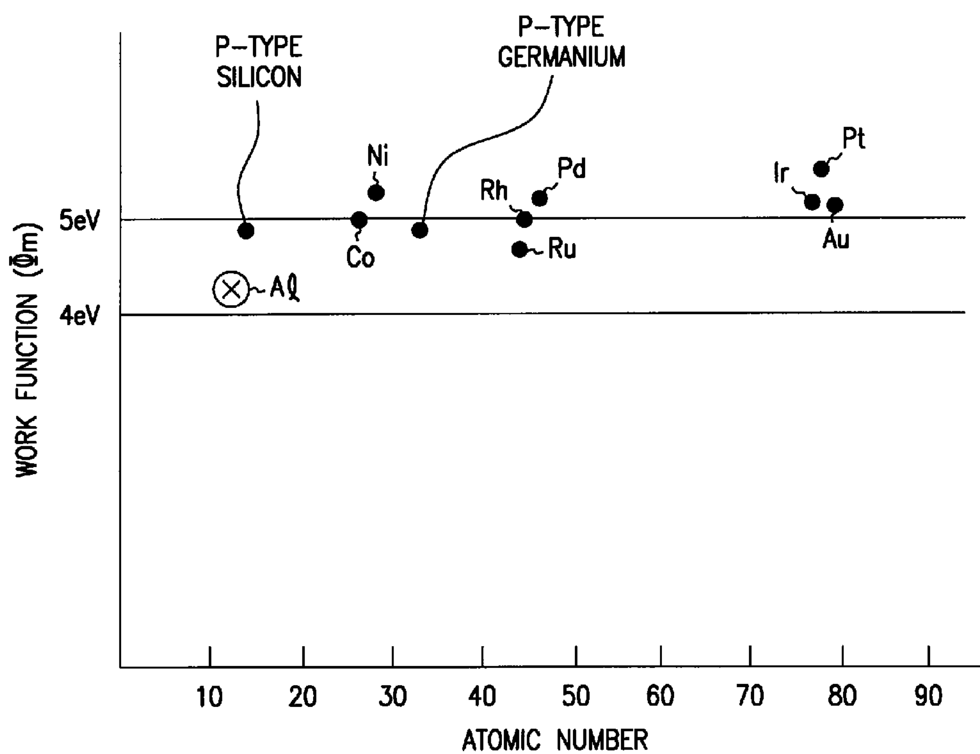


FIG. 4



LARGE WORK FUNCTION METALS

FIG. 5

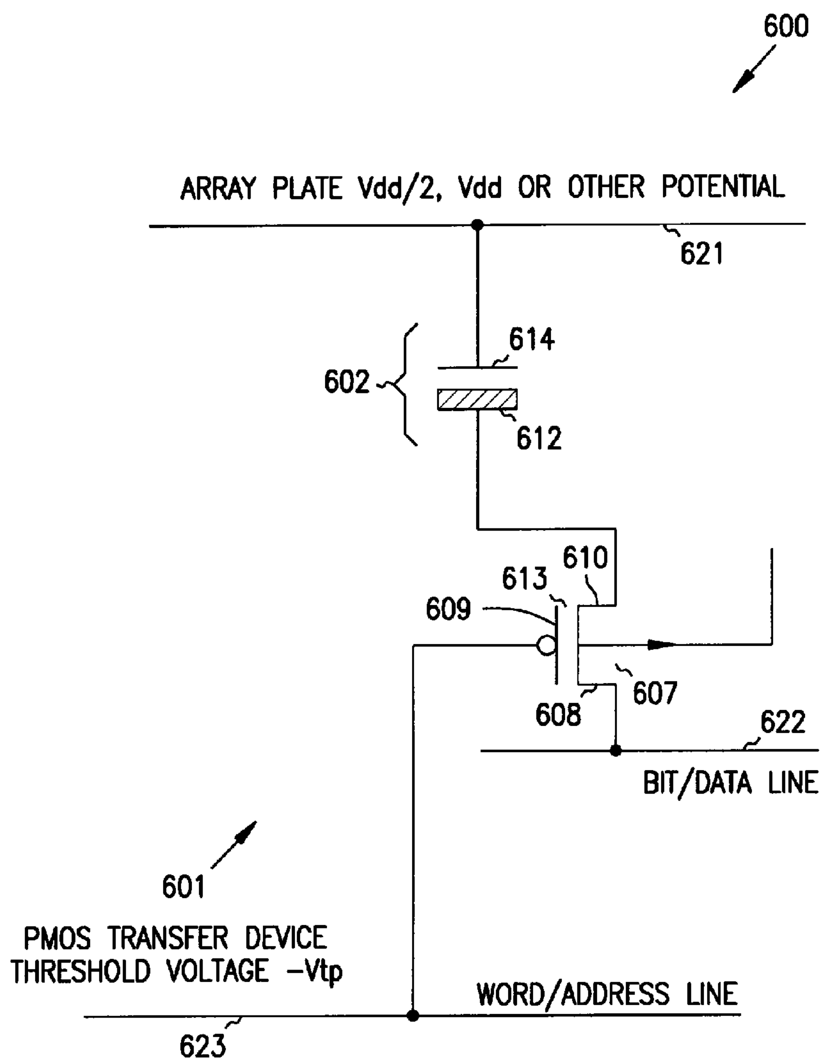


FIG. 6

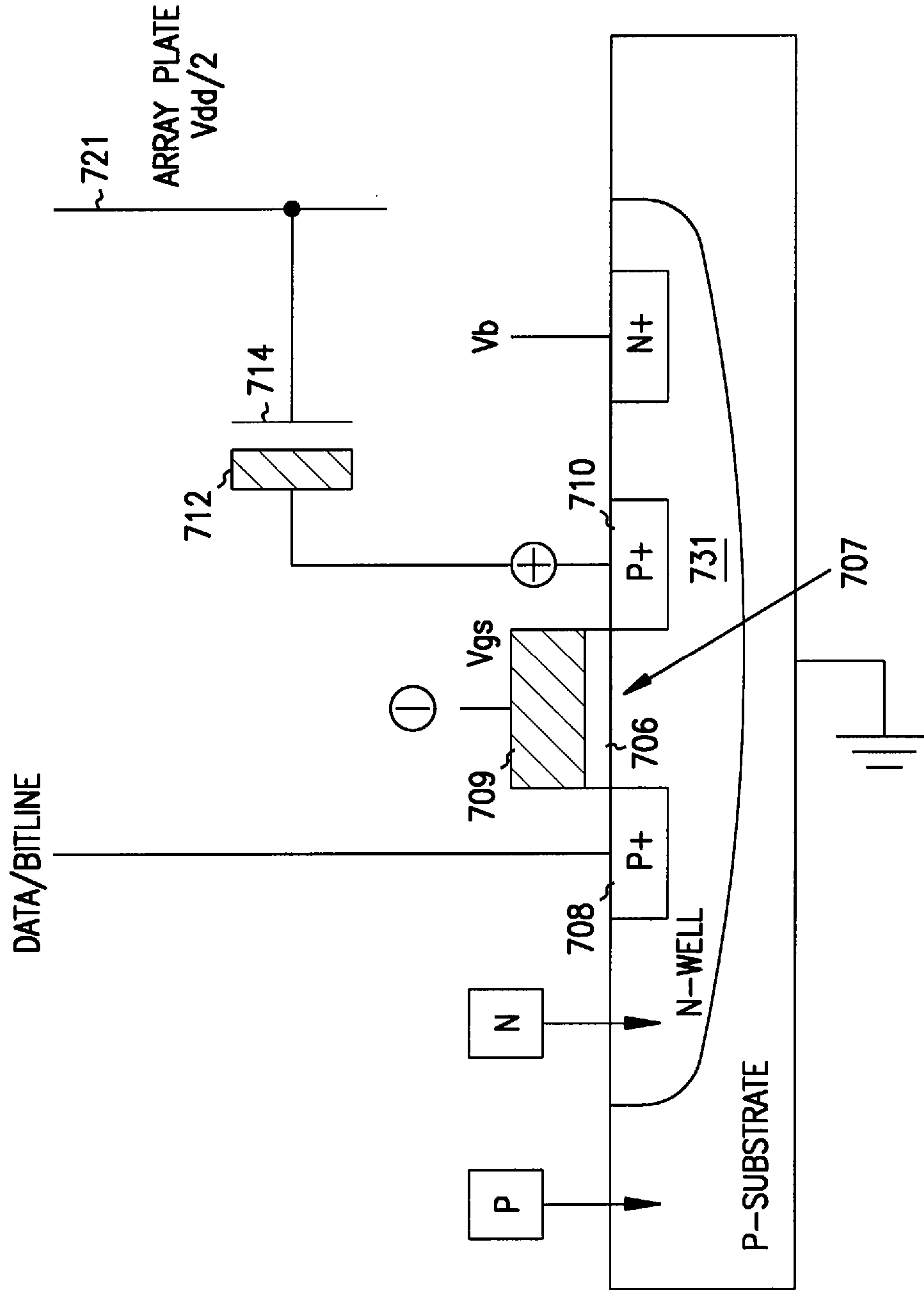


FIG. 7

TECHNIQUE TO CONTROL TUNNELING CURRENTS IN DRAM CAPACITORS, CELLS, AND DEVICES

CROSS-REFERENCE TO RELATED APPLICATIONS

[0001] This application is a continuation of U.S. application Ser. No. 11/267,009, filed Nov. 4, 2005; which is a continuation of U.S. application Ser. No. 10/721,585, filed Nov. 25, 2003, now issued as U.S. Pat. No. 6,979,607; which is a divisional of U.S. application Ser. No. 09/945,310, filed Aug. 30, 2001, now issued as U.S. Pat. No. 6,664,589; each of which is incorporated herein by reference.

[0002] This application is related to the following commonly assigned U.S. patent applications: L. Forbes, "P-CHANNEL DYNAMIC FLASH MEMORY CELLS WITH ULTRATHIN TUNNEL OXIDES," 09/514,627, filed Feb. 28, 2000, now issued as U.S. Pat. No. 6,384,448; L. Forbes, "STATIC NVRAM MEMORY CELL WITH ULTRATHIN ULTRA THIN TUNNEL OXIDES," Ser. No. 09/515,630, filed Feb. 29, 2000, now issued as U.S. Pat. No. 6,639,835; L. Forbes and K. Y. Ahn, "LOW VOLTAGE FIELD (IN SYSTEM) PROGRAMMABLE LOGIC ARRAY PLA'S WITH ULTRATHIN TUNNEL OXIDES," Ser. No. 09/515,759, filed Feb. 29, 2000, now issued as U.S. Pat. No. 6,605,961; L. Forbes and k. Y. Ahn, "LOW VOLTAGE PROGRAMMABLE LOW VOLTAGE MEMORY ADDRESS AND DECODE CIRCUITS WITH ULTRATHIN TUNNEL OXIDES FOR FAULT CORRECTION," Ser. No. 09/515,115, filed Feb. 20, 2000, now issued as U.S. Pat. No. 6,351,428; each of which disclosure is herein incorporated by reference.

FIELD OF THE INVENTION

[0003] The present invention relates generally to integrated circuits, and in particular to techniques to control tunneling currents in DRAM capacitors, cells, and devices.

BACKGROUND OF THE INVENTION

[0004] Field-effect transistors (FETs) are typically produced using a standard complementary metal-oxide-semiconductor (CMOS) integrated circuit fabrication process. As is well known in the art, such a process allows a high degree of integration such that a high circuit density can be obtained with the use of relatively few well-established masking and processing steps. A standard CMOS process is typically used to fabricate FETs that each have a gate electrode that is composed of—type conductively doped polycrystalline silicon (polysilicon) material or other conductive materials.

[0005] The modern memory cell is composed of one transistor, such as the above described FET, and one capacitor. This modern form of the memory cell is referred to as dynamic random access memory (DRAM). In a DRAM, stored charge on the capacitor represents represent a binary one or zero while the transistor, or FET, acts as the switch interposed between the bit line or digit line and capacitor. The capacitor array plate or common node is typically charged to Vcc/2 (Vcc also written as Vdd), and therefore the charge stored on the capacitor for logic 1 is q=C*Vcc/2 and for a logic zero the stored charge is q=−C*Vcc/2 the charge is negative with respect to Vcc/2 common node voltage. The bit line or digit line connects to a multitude of transistors. The gate of the access transistor is connected to a word or row line. The wordline connects to a multitude of transistors.

[0006] In conventional DRAMS using NMOS access transistors, the transmission of a 1 or Vcc in writing a 1 into the capacitor (i.e., charging the capacitor to Vcc, though the total voltage across the capacitor is Vcc/2 as the array plate is kept at Vcc/2) is degraded unless a gate voltage higher than Vcc or Vdd is used. If the gate voltage was just kept at Vdd or Vcc the amount of voltage on the capacitor plate connected to the transistor would only be Vdd-Vtn (where Vtn is the threshold voltage). Using an n-channel access devices requires the gate voltage of the n-channel transistor be raised to Vdd+Vtn where Vtn is the threshold voltage of the NMOS transistor. This will allow the capacitor plate to see a full Vdd, e.g. [(Vdd+Vtn)−Vtn]=Vdd. Similarly for the PMOS access transistors the transmission of a zero or Vss is degraded, and the voltage of the PMOS gate has to be lowered to Vss−Vtp. The preferred voltage applied to the gate of the PMOS device when turned on in this invention is −Vtp, or more negative than Vtp. Applying this voltage to the PMOS transistor turns it on and therefore a 1 or a 0 can be written into the capacitor. If the plate connected to the PMOS is charged to Vcc or Vdd then the capacitor stores a 1, and if the plate connected to the PMOS is charged Vss then the capacitor stores a 0. Normally the array plate of the capacitor is tied to Vcc/2 and the voltage across the capacitor is Vcc/2.

[0007] The use of PMOS devices in DRAM memory cells is in itself not new, in fact the original patent (U.S. Pat. No. 3,387,286 "FIELD EFFECT TRANSISTOR MEMORY," R. H. Dennard, 4 Jun. 1968) described both the use of NMOS and PMOS devices. In 1970, the newly formed Intel Company publicly released the 1103, the first DRAM (Dynamic Random Access Memory) chip (1K bit PMOS dynamic RAM ICs), and by 1972 it was the best selling semiconductor memory chip in the world, defeating magnetic core type memory. The first commercially available computer using the 1103 was the HP 9800 series. These devices however were based on an old technology with gate oxides in the range of 1000 angstroms, 0.1 micron, or 100 nm. PMOS devices were used because of the normally accumulated surface on n-type wafers, techniques had not yet been fully developed to control the surface inversion in the field regions of p-type wafers. With such thick gate insulators and capacitor dielectrics there was and is little consideration and concern about tunneling leakage currents.

[0008] With the development of the LOCOS process and field implantations to control surface inversion on p-type wafers the industry changed to NMOS technology and then CMOS technology on p-type wafers. Subsequent developments and scaling of devices to below 0.1 micron, or 100 nm, dimensions have resulted in the use of ultrathin gate oxides and capacitor dielectric insulators, as low as 12 angstroms, or 1.2 nm. Such ultrathin insulators can result in large tunneling currents, in the case of silicon oxide as large as 1.0 A/cm^2 (S. M. Sze, "Physics of semiconductor devices," Wiley, N.Y., 1981, pp. 402-407; T. P. Ma et al., "Tunneling leakage current in ultrathin (<4 nm) nitride/oxide stack dielectrics," IEEE Electron Device Letters, vol. 19, no. 10, pp. 388-390, 1998). While such leakage or tunneling currents may not cause faults in microprocessors and logic circuits (R. Chau et al., "30 nm physical gate

length CMOS transistors with 1.0 ps n-MOS and 1.7 ps p-MOS gate delays," IEEE Int. Electron, Devices Meeting, San Francisco, pp. 45-48, December 2000) they are intolerable in DRAM devices, capacitors and cells.

[0009] FIG. **1**A, illustrates a conventional DRAM cell **100**. As shown in FIG. **1**A, the conventional DRAM cell includes a transistor **101** and a capacitor cell **102**. A gate **103** for the transistor **101** is separated from the channel **104** of the transistor **100** by an insulator **106**, such as an oxide. The channel region **104** of the transistor separates a source region, or first source/drain region **108** from a drain region, or second source/drain region **110**. As shown in FIG. **1**A, the drain region **110** is coupled to a first plate or capacitor plate **112** of the capacitor cell **102**. A second plate, or array plate **114** of the capacitor cell **102** is coupled to Vdd/2. As stated above, these cells depend upon charge storage on capacitance nodes. FIG. **1**A illustrates tunneling currents which are leakage currents that will discharge the cells resulting in shortened retention times and/or lost data and faults. FIG. **1**A further illustrates that a cause of leakage currents is tunneling from the source/drain of the transfer device which is connected to the capacitor plate to the gate of the transistor when the transistor is off.

[0010] As illustrated in FIG. **1**B, if a zero is stored in the capacitor cell **102**, then the drain **110** of the transistor will be at zero or ground potential, but the gate **103** of the transistor when turned off will be a potential Vdd. This results in a large positive potential between the source/drain at ground, e.g. drain **110** and the gate **103** at potential+Vdd which can result in tunneling leakage currents. These leakage currents would tend to make the capacitor electrode more positive and can result in data errors.

[0011] Also, tunneling leakage currents from the gate **103** to substrate/channel **104** when the transistor **101** is turned on with a large negative gate **103** to source **108** voltage will result in excessive gate currents. While the tunneling current of one gate **103** may be very small, modern DRAM arrays have a large number of capacitor cells **102** and transfer devices **101**. Summed over an entire array, this leakage current, which may be up to 1 A/cm^2, will result in excessive power supply currents and power dissipation.

[0012] Therefore, there is a need in the art to provide improved techniques for controlling tunneling currents in DRAM capacitors, cells and devices. Such improved techniques should take into power supply currents and power dissipation issues.

BRIEF DESCRIPTION OF THE DRAWINGS

[0013] FIGS. **1**A-**1**B, illustrate a conventional DRAM cell.

[0014] FIG. **2** is an energy band diagram illustrating the "mid-gap" metals used for optimizing NMOS and PMOS transistor threshold voltages according to the prior art.

[0015] FIG. **3**A is an energy band diagram illustrating direct band to band tunneling with low voltages across the gate oxides or gate insulators in conjunction with a p-type semiconductor gate or p-type capacitor storage nodes having large electron affinities or work functions according to the teachings of the present invention.

[0016] FIG. **3**B is an energy band diagram illustrating direct band to band tunneling with low voltages across the gate oxides or gate insulators in conjunction with metal gate or metal capacitor storage nodes having large work functions according to another embodiment of the present invention.

[0017] FIG. **4** is a graph plotting electron affinity versus band gap energy of silicon, carbide, and oxygen related compounds.

[0018] FIG. **5** is a graph plotting work function versus atomic number for large work function materials.

[0019] FIG. **6** illustrates one embodiment for DRAM device, or transistor according to the teachings of the present invention.

[0020] FIG. **7** illustrates a memory cell according to the teachings of the present invention.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0021] In the following detailed description of the invention, reference is made to the accompanying drawings which form a part hereof, and in which is shown, by way of illustration, specific embodiments in which the invention may be practiced. The embodiments are intended to describe aspects of the invention in sufficient detail to enable those skilled in the art to practice the invention. Other embodiments may be utilized and changes may be made without departing from the scope of the present invention. In the following description, the terms wafer and substrate are interchangeably used to refer generally to any structure on which integrated circuits are formed, and also to such structures during various stages of integrated circuit fabrication. Both terms include doped and undoped semiconductors, epitaxial layers of a semiconductor on a supporting semiconductor or insulating material, combinations of such layers, as well as other such structures that are known in the art. The following detailed description is not to be taken in a limiting sense, and the scope of the present invention is defined only by the appended claims.

[0022] In the past we have disclosed the use of this direct band to band tunneling current in PMOS devices for flash memory type devices and cells (L. Forbes, "P-CHANNEL DYNAMIC FLASH MEMORY CELLS WITH ULTRATHIN TUNNEL OXIDES," Ser. No. 09/514,627, filed Feb. 28, 2000, now U.S. Pat. No. 6,384,448; L. Forbes, "STATIC NVRAM MEMORY CELL WITH ULTRA THIN TUNNEL OXIDES," Ser. No. 09/515,630, filed Feb. 29, 2000, now U.S. Pat. No. 6,639,835; L. Forbes and K. Y. Ahn, "LOW VOLTAGE PLA'S WITH ULTRATHIN TUNNEL OXIDES," Ser. No. 09/515,759, filed Feb. 29, 2000, now U.S. Pat. No. 6,605,961; L. Forbes and K. Y. Ahn, "PROGRAMMABLE LOW VOLTAGE MEMORY ADDRESS AND DECODE CIRCUITS WITH ULTRATHIN TUNNEL OXIDES," Ser. No. 09/515,115, filed Feb. 20, 2000, now U.S. Pat. No. 6,351,428), the intent there being to increase the endurance of flash memory type cells since direct band to band tunneling will not result in electron collisions in the oxide and damage to the oxide as occurs in F-N tunneling.

[0023] Prior art in the use of metals with work functions larger than aluminum or n-type polysilicon have been directed at so called "mid-gap" work functions which make the threshold voltages for both NMOS and PMOS devices symmetrical (see generally, B. Maiti and P. J. Tobin, "Metal

gates for advanced CMOS technology," Proc. Microelectronics Device Technology III, Santa Clara, Calif., 22-23 September, 1999, Soc. of Photo-Optical Instrumentation Engineers, Bellingham Wash., pp. 46-57) or the same magnitude or numeric value. This is illustrated in FIG. **2** showing the position of the Fermi level in the metal falling in the center of the silicon bandgap with no potential difference across the gate insulator. Common mid-gap metal work functions are provided by the refractory metals tungsten, W, and molydenum, Mo.

[**0024**] FIG. **2** is an energy band diagram illustrating the "mid-gap" metals used for optimizing NMOS and PMOS transistor threshold voltages according to the prior art. FIG. **2** is used to illustrate a metal gate **209**, such as Tungsten W (work function 4.6 eV) or Molybdenum Mo (work function 4.7 eV) in a DRAM cell separated by an oxide **201** from a channel region **207** in either an n-type (PMOS transistor) or a p-type (NMOS transistor) substrate. As shown in FIG. **2**, the metal/semiconductor work function differences can be expressed as follows. For NMOS devices 4.7V−5.0 eV=−0.3 eV, for PMOS devices 4.7-4.4 eV=+0.3 eV. FIG. **2** illustrates the position of the Fermi level in the metal falling in the center of the silicon bandgap with no potential difference across the gate insulator. As stated above, common mid-gap metal work functions are provided by the refractory metals tungsten, W, and molybdenum, MO. However, these prior art techniques still do not solve the problem of low leakage current, which may be up to 1 A/cm^2, and will result in excessive power supply currents and power dissipation.

[**0025**] In the present invention, the intent is to utilize the larger tunneling barriers and lower voltages than used in flash memory devices to limit these tunneling leakage currents to levels which are acceptable in DRAM devices, cells and capacitors.

[**0026**] FIG. **3**A is an energy band diagram illustrating direct band to band tunneling with low voltages across the gate oxides or gate insulators in conjunction with a p-type semiconductor gate or p-type capacitor storage nodes **309** having large electron affinities or work functions according to the teachings of the present invention. FIG. **3**A illustrates a p-type semiconductor gate or capacitor storage node/plate **309** separated by an insulator, e.g. an oxide **301**, from a channel region/substrate **307** or second capacitor storage node/plate **307**. According to the teachings of the present invention, the p-type semiconductor gate or capacitor **309** includes polycrystalline semiconductor plates selected from the group consisting of p-doped silicon, p-doped germanium, p-doped silicon germanium compounds, p-doped silicon carbide, p-doped silicon oxycarbide compounds, p-doped gallium nitride compounds, and p-doped gallium aluminum nitride compounds. According to the teachings of the present invention, the tunneling barriers in the structure of FIG. **3**A are much larger than in conventional NMOS devices and capacitor plates doped n-type. As one of ordinary skill in the art will understand upon reading this disclosure, these much larger tunneling barriers will result in tunneling currents which are orders of magnitude smaller at the same electric fields across the gate and/or capacitor insulators **301**.

[**0027**] In fact, according to the teachings of the present invention, the larger barriers and lower operating voltages will preclude Fowler-Nordheim (F-N) tunneling and the primary tunneling mechanism will be limited to direct band-to-band tunneling.

[**0028**] As discussed above, a number of previous works by the current inventors have disclosed the use of direct band-to-band tunneling current in PMOS devices for flash memory type devices and cells. However, there the intent was to increase the endurance of flash memory type cells since direct band-to-band tunneling will not result in electron collisions in the oxide and damage to the oxide as occurs in F-N tunneling. FIG. **3**A illustrates the direct band-to-band tunneling with low voltages across the gate oxides or gate insulators **301**.

[**0029**] In the present invention, the intent is to use the larger tunneling barriers and lower voltages than used in flash memory devices to limit these tunneling leakage currents to levels which are acceptable in DRAM devices, cells and capacitors.

[**0030**] FIG. **3**B is an energy band diagram illustrating direct band to band tunneling with low voltages across the gate oxides or gate insulators in conjunction with metal gate or metal capacitor storage nodes having large work functions according to another embodiment of the present invention. FIG. **3**B illustrates a metal gate or metal capacitor storage node/plate **309** separated by an insulator, e.g. an oxide **301**, from a channel region/substrate **307** or second capacitor storage node/plate. According to the teachings of the present invention, the metal gate or metal capacitor storage node/plate **309** includes a metal gate selected from the group consisting of cobalt, nickel, ruthenium, rhodium, palladium, iridium, platinum and gold. Alternatively, in one embodiment of the present invention, the metal gate or metal capacitor storage node/plate **309** includes a metallic nitride gate selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, and molybdenum nitride.

[**0031**] In contrast to the previous work, the present invention utilizes p-type semiconductor or metal gates or capacitor plates with work functions larger than those of n-type doped polysilicon (4.1 eV) or the commonly used aluminum metal in MOS technology (4.1 eV). Voltages applied to the gates or plates are lower than 3.2 Volts so the primary tunneling mechanism is restricted to direct band to band tunneling (see generally, T. P. Ma et al., "Tunneling leakage current in ultrathin (<4 nm) nitride/oxide stack dielectrics," IEEE Electron Device Letters, vol. 19, no. 10, pp. 388-390, 1998).

[**0032**] FIG. **4** is a graph plotting electron affinity versus band gap energy of silicon, carbide, and oxygen related compounds. As shown in FIG. **4**, silicon dioxide is an insulator with a relative dielectric constant of 3.9, energy gap of approximately 9.0 eV, and electron affinity of 0.9 eV. In a conventional flash memory, electrons stored on the polysilicon floating gate see a large tunneling barrier of about 3.2 eV. This value is the difference between the electron affinities of silicon (4.1 eV) and SiO_2 (0.9 eV). This is a relative large barrier which requires high applied electric fields for electron injection. SiO has a dielectric constant close to that of SiO_2 which, as stated above, has a value near 3.9. Also, as shown in FIG. **4**, SiO has a band gap of approximately 3.2 eV and an estimated electron affinity of 3.5 eV. Accordingly, as shown in FIG. **4**, the x in SiOx can be varied to produce a range of electron affinities and

poly-Si/a-SiOx tunneling barriers from 0.6 eV to 3.2 eV. Finally, Crystalline SiC has a band gap of 3 eV and an electron affinity of 3.7 eV. Amorphous SiC or a-SiC and hydrogenated, amorphous a-SiC_x:H films have relatively low conductivity under modest applied electric fields (see generally, F. Dimichelis et al., "Doped amorphous and microcrystalline silicon carbide as wide bandgap material," Symp. On Wide Band Gap Semiconductors, Mat. Res. Soc., Pittsburgh, Pa., pp. 675-680, 1992). Amorphous-$Si_xC_yO_z$, or a-$Si_xC_yO_z$, is a wide band gap insulator with a low dielectric constant (<4), comparable to SiO_2 (see generally, T. Furusawa et al., "Simple reliable Cu/low-k interconnect integration using mechanically-strong low-k dielectric material: silicon-oxycarbide," Proc. IEEE int. Interconnect Technology Conf, pp. 222-224, June 2000). No measurements have been reported on the electron affinities of amorphous films of silicon oxycarbide but projections can be made based on the electron affinities and band gaps of SiO_2 and SiC. As shown in FIG. **4**, the electron affinity of a-$Si_xC_yO_z$ should vary from that of silicon dioxide (0.9 eV) to that of the silicon carbide (3.7 eV). This means that the electron barrier between the oxycarbide and silicon (sic, the difference in electron affinities of the pure silicon dioxide and pure silicon carbide) can be varied from roughly 0.4 to 3.2 eV.

[**0033**] FIG. **5** is a graph plotting work function versus atomic number for large work function materials. FIG. **5** is provided to note the relationship of work functions to atomic number and position in the periodic table. FIG. **5** illustrates plots the work function versus atomic number of p-type silicon, aluminum (Al), p-type germanium, cobalt (Co), nickel (Ni), ruthenium (Ru), rhodium (Rh), palladium (Pd), iridium (Ir), platinum (Pt) and gold (Au).

[**0034**] According to the teachings of the present invention, the p-doped silicon and silicon germanium, p-doped large band-gap semiconductors, metals with large work functions, and metallic nitrides with large work functions are fabricated using conventional process techniques.

[**0035**] FIG. **6** illustrates one embodiment for DRAM device **600** including a transistor **601** according to the teachings of the present invention. As shown in FIG. **6**, a transistor **601** is provided having a first source/drain region **608** and a second source/drain region **610**. According to the embodiment shown in FIG. **6**, the first **608** and the second **610** source/drain region include source/drain regions, **608** and **610**, formed of a material having a large work function. A channel **607** is located between the first and the second source/drain regions, **608** and **610**. A gate **609** opposes the channel **607**. According to the teachings of the present invention, the gate **609** includes a gate **609** formed of a material having a large work function. A gate insulator **613** separates the gate from the channel.

[**0036**] Several embodiments of the present invention can be described in connection with the transistor **601** in FIG. **6**. These several embodiments include a gate **609** having a large work function where the gate material is formed from the group consisting of p-type doped polycrystalline semiconductor material, large work function metals, and large work function metallic nitrides.

[**0037**] As stated above, one of the several embodiments of the present invention, includes the gate **609** of the transistor **601**, formed of a material having a large work function, being a p-type doped polycrystalline semiconductor gate. The embodiment of the present invention, having a large work function, p-type doped polycrystalline semiconductor gate **609** can further include several subsets to this embodiment. In one subset embodiment, the large work function, p-type doped polycrystalline semiconductor gate **609** includes p-doped germanium. In another subset embodiment, the large work function, p-type doped polycrystalline semiconductor gate **609** includes p-doped silicon germanium compounds. In another subset embodiment, the large work function, p-type doped polycrystalline semiconductor gate **609** includes p-doped silicon carbide.

[**0038**] FIG. **6** can similarly illustrates another embodiment for DRAM device **600**, or transistor **601** according to the teachings of the present invention. As shown in FIG. **6** a transistor **601** is provided having a first source/drain region **608** and a second source/drain region **610**. According to the embodiment shown in FIG. **6**, the first **608** and the second **610** source/drain region include source/drain regions, **608** and **610**, formed of a material having a large work function. A channel **607** is located between the first and the second source/drain regions, **608** and **610**. A gate **609** opposes the channel **607**. According to the teachings of the present invention, the gate **609** includes a gate **609** formed of a material having a large work function. In this alternative embodiment, the gate includes a metal gate selected from the group consisting of cobalt, nickel, ruthenium, rhodium, palladium, iridium, platinum and gold. Further, the metal gate can include a metallic nitride gate selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, and molybdenum nitride.

[**0039**] As shown in FIG. **6**, the above described transistor **601** forms part of a memory cell **600**. According to the teachings of the present invention, the memory cell is a DRAM cell. In one embodiment of the present invention, the gate insulator is less than 20 Angstroms thick.

[**0040**] As shown in FIG. **6**, the memory cell **600** includes a capacitor **602** coupled to the second source/drain region **610** wherein a first **612** and a second plate **614** of the capacitor include first and second plates, **612** and **614** respectively, having a large work function. In one embodiment according to the teachings of the present invention, at least one of the first and the second plates, **612** and **614** include p-type polysilicon polycrystalline semiconductor plates. In this embodiment, the polycrystalline semiconductor plates, **612** and **614**, are selected from the group consisting of p-doped silicon, p-doped germanium, p-doped silicon germanium compounds, p-doped silicon carbide, p-doped silicon oxycarbide compounds, p-doped gallium nitride compounds, and p-doped gallium aluminum nitride compounds.

[**0041**] In an alternative embodiment, at least one of the first and the second plates, **612** and **614** respectively include metal plates. In this embodiment, the metal plates include metal plates selected from the group consisting of cobalt, nickel, ruthenium, rhodium, palladium, iridium, platinum and gold. In still another embodiment of the present invention, the first and the second plates, **612** and **614** include metallic nitride plates. In this embodiment, the metallic nitride plates, **612** and **614** include metallic nitride plates selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, and molybdenum nitride.

[**0042**] FIG. **7** illustrates a memory cell **700** according to the teachings of the present invention. As shown in FIG. **7**,

memory cell **700** includes a PMOS transistor **701** formed in an n-type well **731**. As shown in FIG. **7**, the PMOS transistor **701** includes a first source/drain region **708**, and a second source/drain region **710**, where the first and the second source/drain region, **708** and **710** include source/drain regions having a large work function. A channel is **707** located between the first and the second source/drain regions, **708** and **710**. A gate **709** opposes the channel **707**. The gate includes a gate having a large work function. A gate insulator **706** separates the gate from the channel **707**. In one embodiment, the gate insulator **706** is less than 20 Angstroms thick. As shown in FIG. **7**, the memory cell **700** further includes a capacitor **703** coupled to the second source/drain region **710** wherein a first and a second plate of the capacitor, **712** and **714** includes first and second plates having a large work function.

[**0043**] As described above, embodiments of the present invention include first and the second p-type polysilicon polycrystalline semiconductor plates selected from the group consisting of p-doped silicon, p-doped germanium, p-doped silicon germanium compounds, p-doped silicon carbide, p-doped silicon oxycarbide compounds, p-doped gallium nitride compounds, and p-doped gallium aluminum nitride compounds.

[**0044**] Alternatively, the first and the second plates **712** and **714** include metal plates selected from the group consisting of cobalt, nickel, ruthenium, rhodium, palladium, iridium, platinum and gold. Alternatively still, the first and the second plates **712** and **714** include metallic nitride plates selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, and molybdenum nitride.

[**0045**] Also, as described above, embodiments of the present invention include a gate **709** that includes a metal gate **709** selected from the group consisting of cobalt, nickel, ruthenium, rhodium, palladium, iridium, platinum and gold. Alternatively, the gate **709** includes a metallic nitride gate **709** selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, and molybdenum nitride. Alternatively still, the gate **709** includes a p-type polycrystalline semiconductor gate selected from the group consisting of p-doped silicon, p-doped germanium, p-doped silicon germanium compounds, p-doped silicon carbide, p-doped silicon oxycarbide compounds, p-doped gallium nitride compounds, and p-doped gallium aluminum nitride compounds.

[**0046**] In one embodiment of FIG. **7**, the n-type well **731** is tied to a positive voltage which is less than a power supply voltage. In an alternative embodiment of FIG. **7**, the n-type well **731** is tied to a voltage which is equal to a power supply voltage. In still another embodiment of the present invention, the n-type well **731** is tied to a voltage which is greater than a power supply voltage.

[**0047**] Using an array plate voltage of Vcc/2 serves to reduce the electric field across the capacitor dielectric to reduce dielectric leakage currents, like tunneling and reduce the probability of dielectric breakdown. Here however if the plates are made of different materials the array plate might be tied to Vcc and the large work function of the other individual capacitor plate used to reduce the tunneling leakage currents since there would either be no electric field or voltage across the dielectric when a 1 was stored in the capacitor or only a negative potential of magnitude Vcc when a zero is stored in the capacitor. If only a negative potential difference is used then the large work function plate material will reduce the tunneling leakage current. If both the array plate and capacitor plate are made of the same large work function material then an array plate potential of Vcc/2 can be used since either plate will have a large work function and it will be difficult to cause electron tunneling from either. If the array plate is not of the same material and is not a high work function material then an intermediate value of array plate potential other than Vcc/2 might be an optimum choice. The disclosure is not so limited. For purposes of illustration we will assume the plates are of the same material and the array plate is at a potential of Vcc/2. By using capacitor plate materials with large work functions, as shown in FIGS. **6** and **7**, the tunneling leakage currents of the storage capacitors can be eliminated.

[**0048**] The use of a PMOS transfer device with a P+ source/drain region with a large work function will result in minimal tunneling currents to the gate or eliminate tunneling leakage currents. According to the teachings of the present invention, the P+ source/drain region can be formed of any of the semiconductor materials described herein having a large work function.

[**0049**] Tunneling leakage from the gate can be avoided or eliminated by using gate materials with a large work function. These tunneling currents can also be reduced by biasing the n-well at a more negative potential or less than the power supply voltage Vdd; however, this can result in extra transistor subthreshold leakage since the source to n-well will be forward biased. Biasing the n-well to a potential less than Vdd will however result in less source/drain junction leakage when a zero is stored in the cell since the reverse bias between the source/drain and well will be smaller. Biasing the n-well more positive or above Vdd will result in less junction leakage tending to reduce the cell capacitor plate to voltages below Vdd when a one is stored on the capacitor plate. A variety of well potentials can thus be employed to meet different application requirements and the disclosure is not so limited by any particular n-well potential.

[**0050**] The use of large work function capacitor electrode plate materials, large work function gate materials, and large work function P+ source/drain regions have been described for the elimination of direct band to band tunneling leakage currents in DRAM memory cells.

METHODS OF THE INVENTION

[**0051**] As will be understood by one of ordinary skill in the art upon reading and studying this disclosure the following methods are included as part of the scope of the present invention. These methods can be fully understood and practiced in reference to the Figures described in detail above. A first method includes a method of forming a memory cell. This method includes forming a PMOS transistor an n-type well. Forming the PMOS transistor includes forming a first and a second source/drain regions separated by a channel. Forming the first and the second source/drain regions includes forming source/drain regions having a large work function. The method further includes forming a gate opposing the channel. According to the teachings of the present invention, forming the gate includes forming a gate having a work function of greater than 4.1 eV. A gate insulator is formed separating the gate from the channel. In one embodiment, the gate insulator is formed to a thickness of less than 20 Angstroms. Finally, the method includes forming a storage device coupled to the second source/drain

region. Forming the storage device includes forming a storage device having a first and a second storage node separated by a dielectric. According to the teachings of the present invention at least one of the first and the second storage nodes has a large work function. In one embodiment, the at least one storage node having a large work function includes a work function greater than 4.1 eV.

[0052] In one embodiment of the above method, forming the PMOS transistor in an n-type well includes coupling the n-type well to a positive voltage which is less than a power supply voltage. In another embodiment of the above method forming the PMOS transistor in an n-type well includes coupling the n-type well to a voltage which is equal to a power supply voltage. In yet another embodiment of the above method forming the PMOS transistor in an n-type well includes coupling the n-type well to a voltage which is greater than a power supply voltage.

[0053] Further, in one embodiment forming the first and the second storage nodes includes forming the first and the second storage nodes of the same material. In one embodiment, forming the first and the second source/drain regions having a large work function includes forming the first and the second source/drain regions with a work function greater than 4.1 eV.

[0054] In one embodiment, forming the first and the second storage nodes includes forming first and second storage nodes which include a p-type polysilicon polycrystalline semiconductor material selected from the group consisting of p-doped silicon, p-doped germanium, p-doped silicon germanium compounds, p-doped silicon carbide, p-doped silicon oxycarbide compounds, p-doped gallium nitride compounds, and p-doped gallium aluminum nitride compounds.

[0055] Alternatively, in one embodiment, forming the first and the second storage nodes includes forming the first and the second storage nodes of a metal selected from the group consisting of cobalt, nickel, ruthenium, rhodium, palladium, iridium, platinum and gold.

[0056] Alternatively still, in one embodiment, forming the first and the second storage nodes includes forming the first and the second storage nodes of a metallic nitride selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, and molybdenum nitride.

[0057] In one embodiment, forming the gate includes forming a metal gate selected from the group consisting of cobalt, nickel, ruthenium, rhodium, palladium, iridium, platinum and gold. In another embodiment of the above method forming the gate includes forming a metallic nitride gate selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, and molybdenum nitride. In another embodiment of the above method forming the gate includes forming a p-type polycrystalline semiconductor gate selected from the group consisting of p-doped silicon, p-doped germanium, p-doped silicon germanium compounds, p-doped silicon carbide, p-doped silicon oxycarbide compounds, p-doped gallium nitride compounds, and p-doped gallium aluminum nitride compounds.

[0058] Another method embodiment of the present invention includes a method for operating a memory cell. This method includes applying a negative voltage to a gate of a PMOS transistor formed in an n-type well. In this embodiment, the PMOS transistor includes a first source/drain region and a second source/drain region. The first and the second source/drain region include source/drain regions having a large work function. A channel is located between the first and the second source/drain regions. A gate opposes the channel. In one embodiment, the gate includes a gate having a large work function. A gate insulator separates the gate from the channel. In one embodiment, the gate insulator is less than 20 Angstroms thick. The method further includes coupling the n-type well to a positive voltage which is less than a power supply voltage. The method further includes reading a charge level of a storage device. The storage device includes a first and a second storage node. At least one of the first and the second storage nodes is formed of a material having a large work function.

[0059] According to the teachings of the present invention, coupling the n-type well to a positive voltage which is less than a power supply voltage achieves lower tunneling charge leakage from the gate.

[0060] Another method embodiment for the present invention includes a method for operating a memory cell. This method includes applying a negative voltage to a gate of a PMOS transistor formed in an n-type well. Again, the PMOS transistor includes a first source/drain region and a second source/drain region. The first and the second source/drain region include source/drain regions having a large work function. A channel located between the first and the second source/drain regions. A gate opposes the channel. In one embodiment, the gate includes a gate having a large work function. A gate insulator separates the gate from the channel. In one embodiment, the gate insulator is less than 20 Angstroms thick. The method further includes coupling the n-type well to a voltage which is equal to a power supply voltage. And, the method includes reading a charge level of a storage device. The storage device includes a first and a second storage node. In one embodiment, at least one of the first and the second storage nodes includes a storage node formed of a material having a large work function.

[0061] According to the teachings of the present invention, coupling the n-type well to a voltage which is equal to a power supply voltage achieves lower tunneling charge leakage from the gate and lower junction leakage from the second source/drain region and storage device when the storage device is not charged.

[0062] Another method embodiment of the present invention includes a method for operating a memory cell. This embodiment includes applying a negative voltage to a gate of a PMOS transistor formed in an n-type well. The PMOS transistor includes a first source/drain region and a second source/drain region. The first and the second source/drain region include source/drain regions formed of a material having a large work function. A channel is located between the first and the second source/drain regions and a gate opposes the channel. In one embodiment, the gate includes a gate having a large work function. A gate insulator separates the gate from the channel. In one embodiment, the gate insulator is less than 20 Angstroms thick. The method further includes coupling the n-type well to a voltage which is greater than a power supply voltage. The method further includes reading a charge level of a storage device. The storage device includes a first and a second storage node. In one embodiment, the first and the second storage nodes includes at least one storage node formed of a material having a large work function.

[0063] According to the teachings of the present invention, coupling the n-type well to a voltage which is greater than a power supply voltage will result in less junction leakage tending to reduce the cell capacitor plate to voltages below Vdd when a one is stored on the capacitor plate.

[0064] As such, one of ordinary skill in the art will understand upon reading this disclosure that a variety of well potentials can thus be employed to meet different application requirements and this disclosure in not so limited by any particular n-well **731** potential.

CONCLUSION

[0065] The above structures and fabrication methods have been described, by way of example and not by way of limitation, with respect to provide improved techniques for controlling tunneling currents in DRAM capacitors, cells and devices. Such improved techniques should take into power supply currents and power dissipation issues.

What is claimed is:

1. A memory cell, comprising:

a storage capacitor, including:

a first plate and a second plate separated by a dielectric;

wherein at least one of the plates includes a p-doped silicon carbide material; and

an access transistor coupled to the storage capacitor.

2. The memory cell of claim 1, wherein the dielectric has an equivalent oxide thickness of less than 20 angstroms.

3. The memory cell of claim 1, wherein the access transistor includes a gate formed from a material with a work function greater than 4.1 eV.

4. The memory cell of claim 3, wherein the gate material includes a metal selected from a group consisting of cobalt, nickel, ruthenium, rhodium, palladium, iridium, platinum, and gold.

5. A memory cell, comprising:

a storage capacitor, including:

a first plate and a second plate separated by a dielectric;

wherein at least one of the plates includes a p-doped silicon oxycarbide material; and

an access transistor coupled to the storage capacitor.

6. The memory cell of claim 5, wherein the dielectric has an equivalent oxide thickness of less than 20 angstroms.

7. The memory cell of claim 5, wherein the access transistor includes a gate formed from a material with a work function greater than 4.1 eV.

8. The memory cell of claim 7, wherein the gate material includes a metal nitride selected from a group consisting of titanium nitride, tantalum nitride, tungsten nitride, and molybdenum nitride.

9. A memory cell, comprising:

a storage capacitor, including:

a first plate and a second plate separated by a dielectric;

wherein at least one of the plates includes a p-doped gallium nitride material; and

an access transistor coupled to the storage capacitor.

10. The memory cell of claim 9, wherein the dielectric has an equivalent oxide thickness of less than 20 angstroms.

11. The memory cell of claim 9, wherein the access transistor includes a gate formed from a material with a work function greater than 4.1 eV.

12. The memory cell of claim 11, wherein the gate material includes a p-doped material selected from a group consisting of p-doped silicon, p-doped germanium, p-doped silicon germanium, p-doped silicon carbide, p-doped silicon oxycarbide, p-doped gallium nitride, and p-doped gallium aluminum nitride.

13. A memory cell, comprising:

a storage capacitor, including:

a first plate and a second plate separated by a dielectric;

wherein at least one of the plates includes p-doped gallium aluminum nitride material; and

an access transistor coupled to the storage capacitor.

14. The memory cell of claim 13, wherein the dielectric has an equivalent oxide thickness of less than 20 angstroms.

15. The memory cell of claim 14, wherein the access transistor includes a gate formed from a material with a work function greater than 4.1 eV, the gate being formed over a gate dielectric with an equivalent oxide thickness of less than 20 angstroms.

16. A dynamic random access memory device comprising:

an array of memory cells, wherein the memory cells include:

a storage capacitor, including:

a first plate and a second plate separated by a capacitor dielectric, wherein the capacitor dielectric has an equivalent oxide thickness of less than 20 angstroms;

wherein at least one of the plates includes a material with a work function greater than 4.1 eV;

a number of PMOS access transistors coupled to the storage capacitors of the memory cells, wherein the PMOS access transistors include:

a first source/drain region;

a second source/drain region;

a channel region coupled between the first and second source/drain regions; and

a gate located over the channel region and separated from the channel region by a gate dielectric, wherein the gate includes a material with a work function greater than 4.1 eV.

17. The dynamic random access memory device of claim 16, wherein the gate dielectric has an equivalent oxide thickness of less than 20 angstroms.

18. The dynamic random access memory device of claim 16, wherein both the first plate and the second plate of the storage capacitor include a material with a work function greater than 4.1 eV.

19. The dynamic random access memory device of claim 16, wherein at least one of the plates includes p-doped gallium aluminum nitride material.

20. The dynamic random access memory device of claim 16, wherein at least one of the plates includes p-doped silicon oxycarbide material.

21. The dynamic random access memory device of claim 16, wherein at least one of the plates includes a p-doped silicon carbide material.

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